

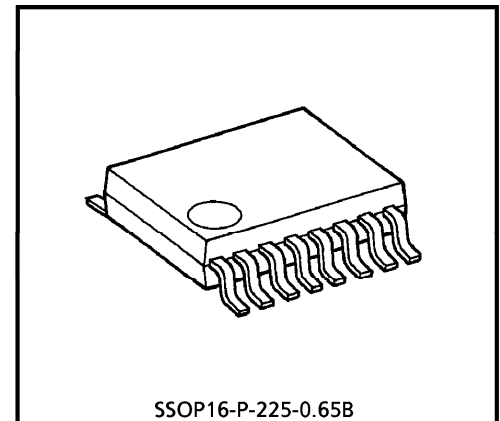
# TA31161FNG

## WIDE-BAND IF DETECTOR IC WITH BUILT-IN HIGH-SPEED MIXER

A wide-band IF detector IC capable of operating at 10.7MHz and designed for the high-speed bit rates used in mobile communication and other systems. This IC is suitable for a receiver for digital mobile communication. High speed mixer, FM detector for 100kHz and high speed response RSSI function are built-in.

### FEATURES

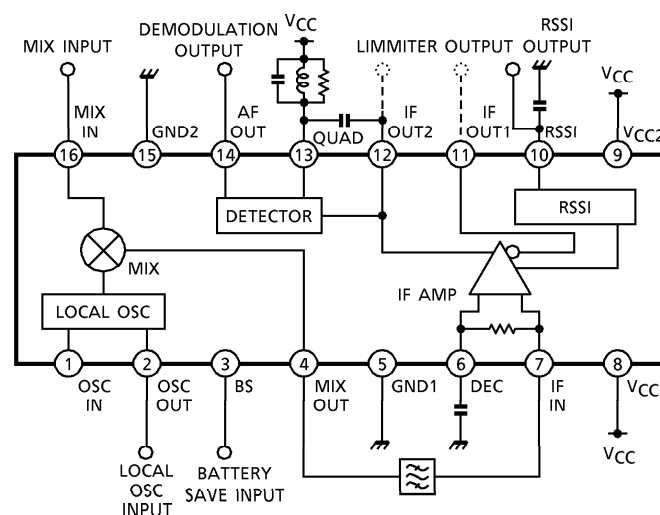
- MIX operating frequency : 40~300MHz
- 12dB sensitivity : 21dB $\mu$ VEMF (input 50 $\Omega$ )
- Current consumption : 5.5mA (Typ.)
- Operating voltage range : 2.3~5.5V
- Small package : SSOP24pin (0.65mm pitch)



SSOP16-P-225-0.65B

Weight : 0.09g (Typ.)

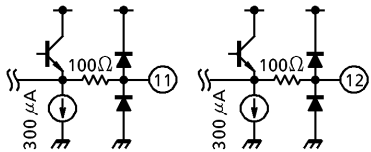
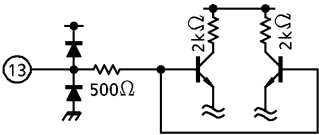
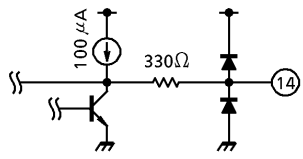
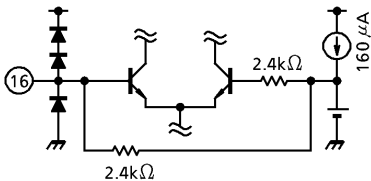
### BLOCK DIAGRAM



TA31161FNG Package is Pb-Free.

## PIN FUNCTION (The values of resistor and capacitor are typ..)

| PIN No. | PIN NAME | FUNCTION                                                                                                                                      | EQUIVALENT INTERNAL CIRCUIT |
|---------|----------|-----------------------------------------------------------------------------------------------------------------------------------------------|-----------------------------|
| 1       | OSC IN   | LOCAL OSC input terminal.<br>Can form an oscillator with an internal transistor and external crystal oscillator.                              |                             |
| 2       | OSC OUT  | Can also operate as a MIX using the signal input externally from Pin 1 or Pin 2.                                                              |                             |
| 3       | BS       | Battery save terminal.<br>Setting this terminal to low results in battery save state. Setting the terminal to high results in activate state. |                             |
| 4       | MIX OUT  | MIX output terminal.<br>Externally connects filters.<br>Output impedance is around 330Ω.                                                      |                             |
| 5       | GND1     | GND terminal                                                                                                                                  | —                           |
| 6       | DEC      | Bias terminal for IF input terminals.<br>Connects external capacitor.<br>The value of the capacitor should be sufficiently large at 10.7MHz.  |                             |
| 7       | IF IN    | IF input terminal.<br>Connected after the filters.                                                                                            |                             |
| 8       | VCC1     | Power supply terminal. (MIX and part of IF)                                                                                                   | —                           |
| 9       | VCC2     | Power supply terminal.<br>(part of IF and detector)                                                                                           | —                           |
| 10      | RSSI     | RSSI output terminal.<br>Voltage output type.                                                                                                 |                             |

| PIN No. | PIN NAME | FUNCTION                                                                      | EQUIVALENT INTERNAL CIRCUIT                                                          |
|---------|----------|-------------------------------------------------------------------------------|--------------------------------------------------------------------------------------|
| 11      | IF OUT1  | IF limiter output terminal.<br>Output of pin 11 and pin 12 is opposite phase. |   |
| 12      | IF OUT2  |                                                                               |                                                                                      |
| 13      | QUAD     | Phase signal input terminal for FM DETECTOR.                                  |   |
| 14      | AF OUT   | Modulation signal output terminal.<br>Output impedance is around 360Ω.        |   |
| 15      | GND2     | GND terminal                                                                  | —                                                                                    |
| 16      | MIX IN   | MIX input terminal.<br>Double-balance MIX.                                    |  |

## 1. LOCAL OSC External Injection Method

Inject as shown in Fig.1, setting the injection level between  $95\text{dB}\mu\text{V}\sim 100\text{dB}\mu\text{V}$ . A built-in buffer AMP. minimizes leakage from the mixer.

Input from pin 1 is possible ; however, when the input frequency is high, the level at pin 2 may not be sufficient, causing a decrease in sensitivity.

In such a case, add resistor R51 and set the input signal so that the signal at pin 2 is adequate. Connect as in Fig.3 to use internal transistor for oscillation.

R51 is the resistor that determines the oscillation current.

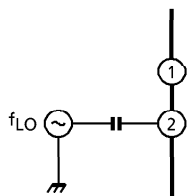


Fig.1

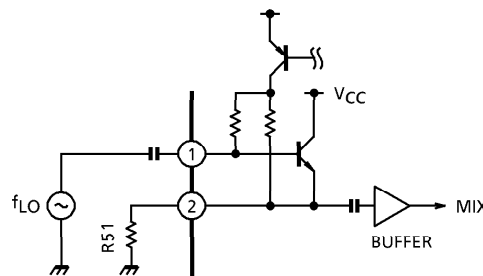


Fig.2

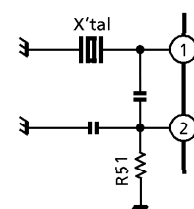


Fig.3

## 2. Overtone Oscillation

Fig.4 shows the basic configuration of the local oscillation circuit using overtone oscillation.

The C51 and L1 tuning circuits prevent crystal fundamental oscillation.

Therefore, set C51 and L1 to inductive at the fundamental frequency and capacitive at the overtone frequency.

Since the level at pin 2 may decrease and the sensitivity may fall at high frequency as with external injection, adjust the oscillation level using R51.

The internal emitter follower circuit can oscillate up to 100MHz.

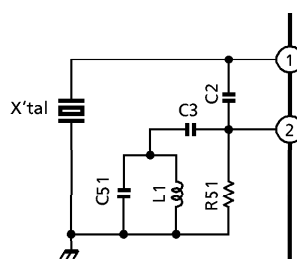


Fig.4

### 3. RSSI Function

The DC voltage output on RSSI varies according to the IF-IN input level. The DC voltage can be lowered by attaching an external resistor.

However, the range of input-output linear relationship cannot be extended.

If an external resistor is attached, the temperature characteristics of RSSI output may change due to the difference of temperature coefficient between the external resistor and the IC itself.

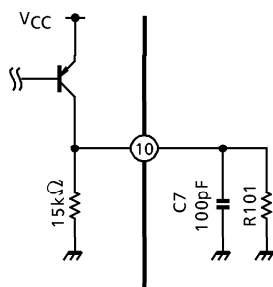
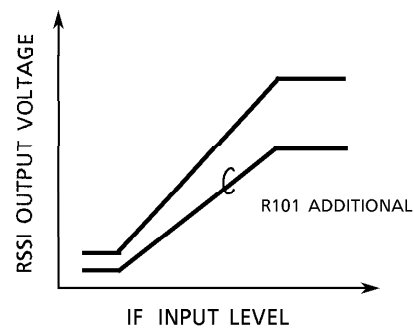


Fig.5



### 4. Disusing Pin Connection

In case of disusing MIX and LOCAL OSC, disusing pin connects as shown in Fig.6.

In case of disusing FM DETECTOR, disusing pin connects as shown in Fig.7.

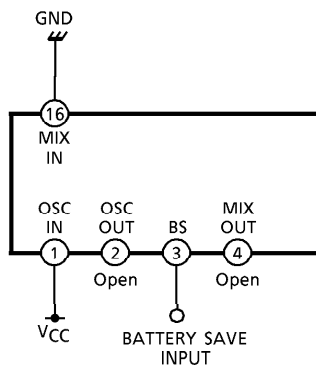


Fig.6

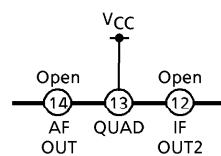


Fig.7

**MAXIMUM RATINGS** (Ta = 25°C)

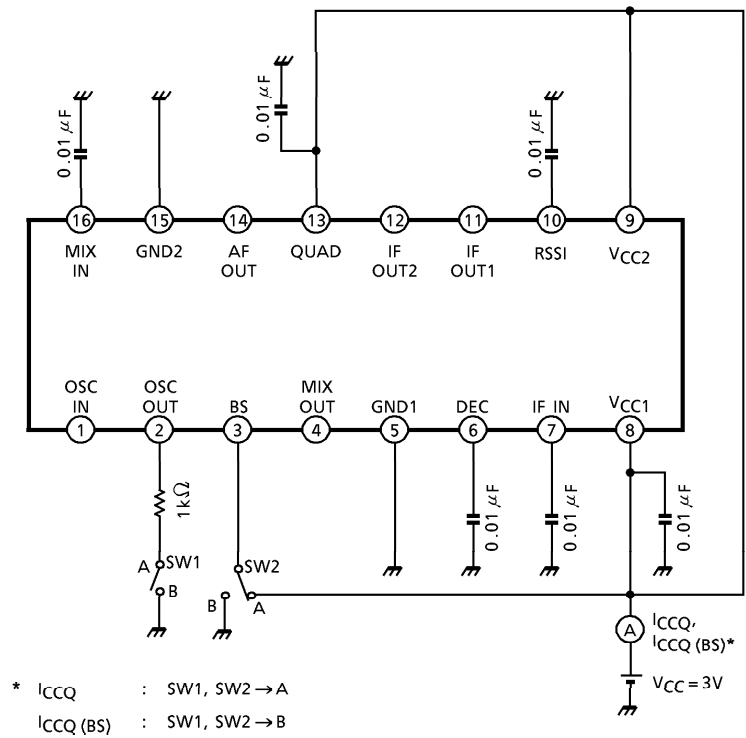
| CHARACTERISTICS       | SYMBOL           | RATINGS | UNIT |
|-----------------------|------------------|---------|------|
| Power Supply Voltage  | V <sub>CC</sub>  | 6       | V    |
| Power Dissipation     | P <sub>D</sub>   | 240     | mW   |
| Operating Temperature | T <sub>opr</sub> | -35~85  | °C   |
| Storage Temperature   | T <sub>stg</sub> | -55~150 | °C   |

**ELECTRICAL CHARACTERISTICS** (Unless otherwise specified V<sub>CC</sub> = 3V, f<sub>IN</sub> (MIX) = 90.7MHz, f<sub>IN</sub> (IF) = 10.7MHz, f<sub>MOD</sub> = 1kHz, Δf = ±100kHz, Ta = 25°C)

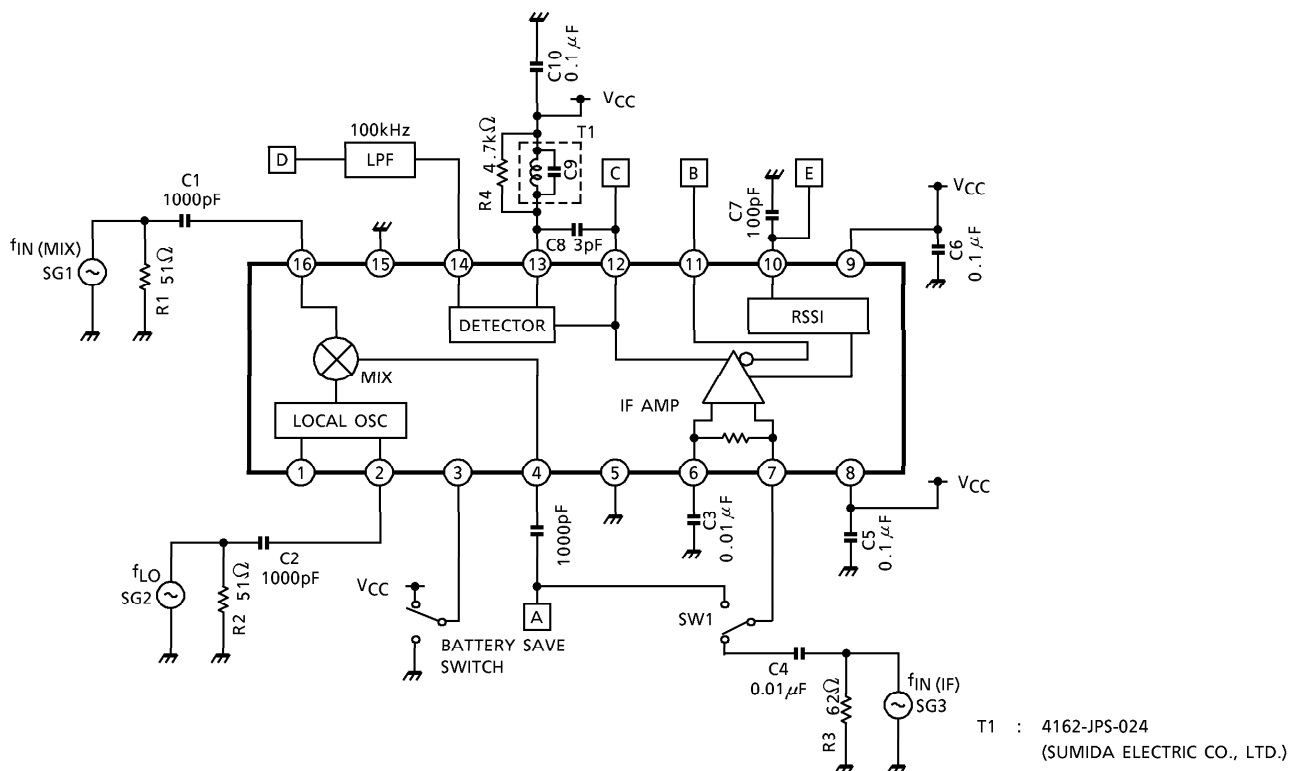
| CHARACTERISTICS                    | SYMBOL                | TEST CIR-CUIT | TEST CONDITION                               | MIN. | TYP. | MAX. | UNIT              |
|------------------------------------|-----------------------|---------------|----------------------------------------------|------|------|------|-------------------|
| Operating Voltage Range            | V <sub>CC opr</sub>   | —             | —                                            | 2.3  | 3    | 5.5  | V                 |
| Current Consumption                | I <sub>CCQ</sub>      | 1             | When local oscillation stopped               | —    | 5.5  | 7.5  | mA                |
| Battery Save Current               | I <sub>CCQ</sub> (BS) | 1             | BS = "L"                                     | —    | 0    | 10   | μA                |
| MIX Operating Frequency            | f <sub>IN</sub>       | —             | —                                            | 40   | 240  | 300  | MHz               |
| MIX Conversion Gain                | G <sub>VC</sub>       | 2             | V <sub>IN</sub> (MIX) = 50dBμV               | 15   | 19   | 23   | dB                |
| MIX Intercept Point                | P <sub>IM</sub>       | —             | V <sub>IN</sub> (MIX) = 80dBμVEMF            | —    | 95   | —    | dBμV              |
| MIX Equivalent Input Resistance    | R <sub>IN</sub> (MIX) | —             | —                                            | —    | 1    | —    | kΩ                |
| MIX Equivalent Input Capacitance   | C <sub>IN</sub> (MIX) | —             | —                                            | —    | 3    | —    | pF                |
| MIX 1dB Compression Level          | DR (MIX)              | —             | MIX input level at G <sub>VC</sub> 1dB down. | —    | 90   | —    | dBμV              |
| MIX Output Resistance              | R <sub>O</sub> (MIX)  | —             | —                                            | —    | 330  | —    | Ω                 |
| LOCAL OSC Operating Frequency      | f <sub>LO</sub>       | —             | —                                            | 40   | —    | 100  | MHz               |
| Recommended Local Input Level      | V <sub>LO</sub>       | —             | —                                            | —    | 100  | —    | dBμV              |
| Local Equivalent Input Resistance  | R <sub>IN</sub> (LO)  | —             | —                                            | —    | 1    | —    | kΩ                |
| Local Equivalent Input Capacitance | C <sub>IN</sub> (LO)  | —             | —                                            | —    | 2.4  | —    | pF                |
| IF Input Resistance Value          | R <sub>IN</sub> (IF)  | —             | —                                            | —    | 330  | —    | Ω                 |
| IF AMP Gain                        | G <sub>V</sub> (IF)   | —             | —                                            | —    | 72   | —    | dB                |
| IF Output Level                    | V <sub>O</sub> (IF)   | 2             | —                                            | 400  | 500  | 600  | mV <sub>p-p</sub> |
| RSSI Variation Width               | V <sub>D</sub> (RSSI) | —             | —                                            | —    | 70   | —    | dB                |
| RSSI Output Resistance             | R (RSSI)              | —             | —                                            | 10.5 | 15   | 19.5 | kΩ                |
| RSSI Output Voltage                | V (RSSI)              | 2             | V <sub>IN</sub> = 70dBμV EMF, Non modulation | 1.0  | 1.2  | 1.4  | V                 |

| CHARACTERISTICS           | SYMBOL    | TEST CIR-CUIT | TEST CONDITION | MIN. | TYP. | MAX.     | UNIT              |
|---------------------------|-----------|---------------|----------------|------|------|----------|-------------------|
| High Level Input Voltage  | $V_H$     | —             | BS             | 2    | —    | $V_{CC}$ | V                 |
| Low Level Input Voltage   | $V_L$     | —             | BS             | GND  | —    | 0.2      |                   |
| Demodulation Output Level | $V_{OD}$  | 2             | —              | 150  | 200  | 260      | mV <sub>rms</sub> |
| Demodulation Frequency    | $f_{DET}$ | —             | —              | —    | 100  | —        | kHz               |
| 12dB Sensitivity          | 12dB SN   | —             | MIX INPUT      | —    | 21   | —        | dB $\mu$ V<br>EMF |
| SN Ratio                  | SN        | —             | MIX INPUT      | —    | 55   | —        | dB                |
| AM Rejection Ratio        | AMR       | —             | MIX INPUT      | —    | 40   | —        | dB                |

TEST CIRCUIT 1



## TEST CIRCUIT 2



Test conditions for mixer conversion gain  $G_{VC}$

SG1  $f_{IN(MIX)} = 90.7\text{MHz}$ ,  $V_{IN(MIX)} = 50\text{dB}\mu\text{V}$  EMF

SG2  $f_{LO} = 80.0\text{MHz}$ ,  $V_{LO} = 100\text{dB}\mu\text{V}$  EMF

$G_{VC}$  = value at point [A] - 50dB

Test conditions for RSSI level output  $V(RSSI)$

SG3  $f_{IN(IF)} = 10.7\text{MHz}$ ,  $V_{IN(IF)} = 70\text{dB}\mu\text{V}$  EMF

$V(RSSI)$  = voltage at point [E]

Test conditions for IF output level  $V_O(IF)$

SG3  $f_{IN(IF)} = 5\text{MHz}$ ,  $V_{IN(IF)} = 80\text{dB}\mu\text{V}$  EMF

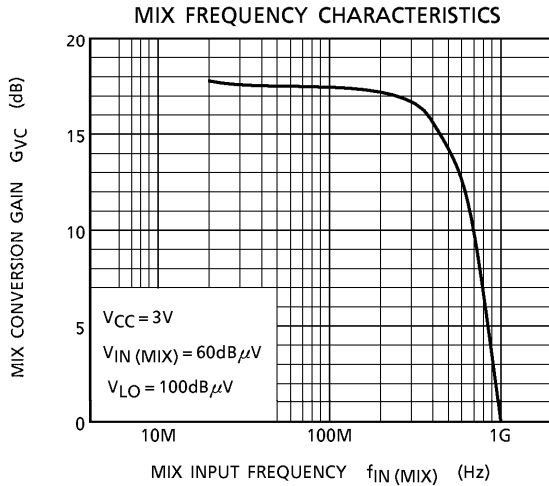
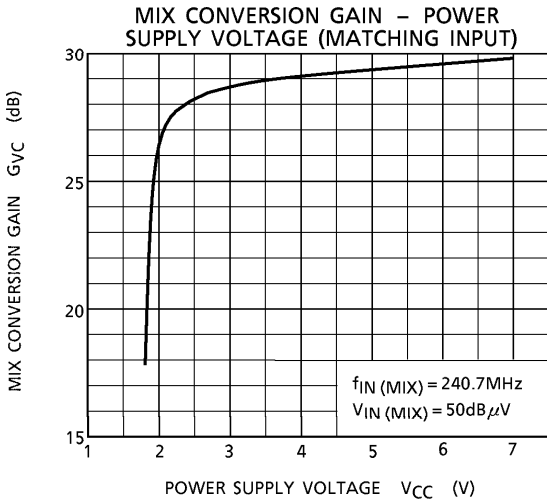
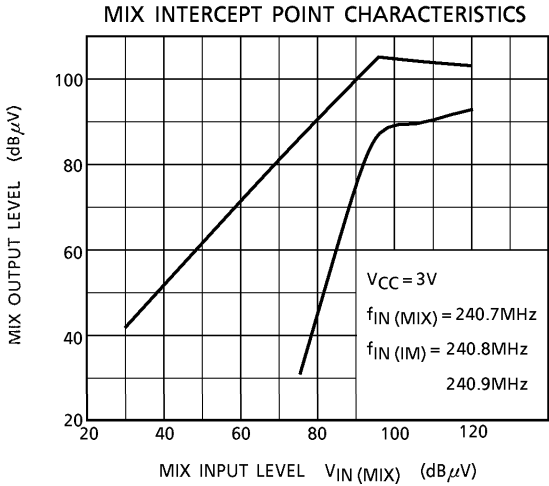
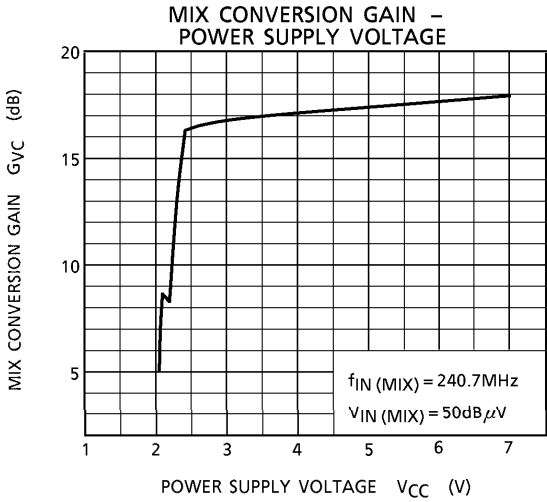
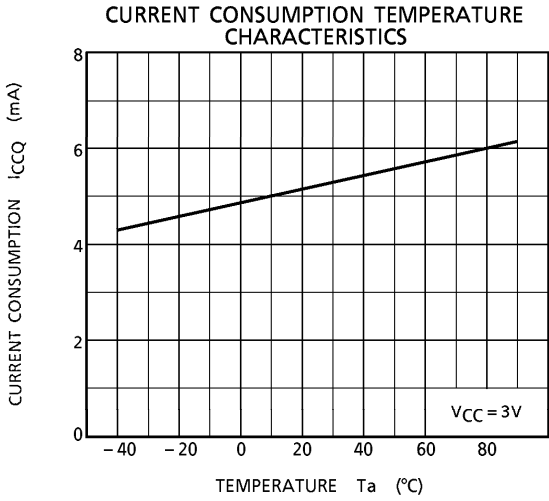
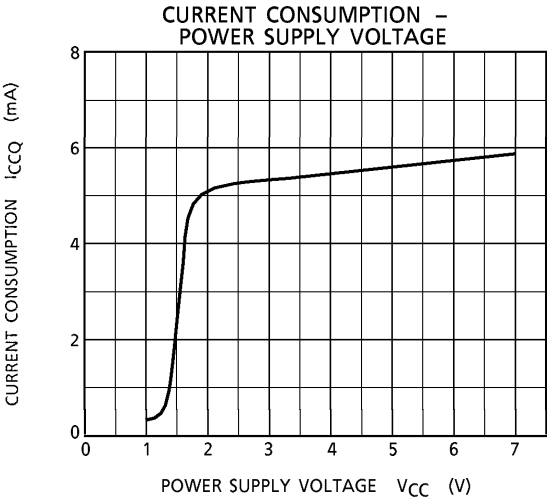
$V_O(IF)$  = peak output level at point [B] or point [C]

Test conditions for detect output  $V_{OD}$

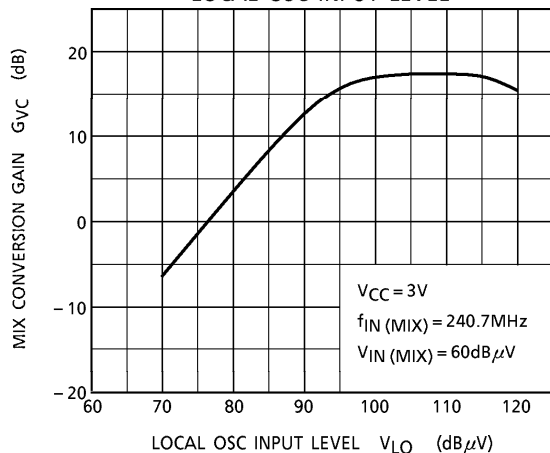
SG3  $f_{IN(IF)} = 10.7\text{MHz}$ ,  $\Delta f = \pm 100\text{kHz}$ ,  $f_{MOD} = 1\text{kHz}$ ,  $V_{IN(IF)} = 80\text{dB}\mu\text{V}$  EMF

$V_{OD}$  = voltage at point [D]

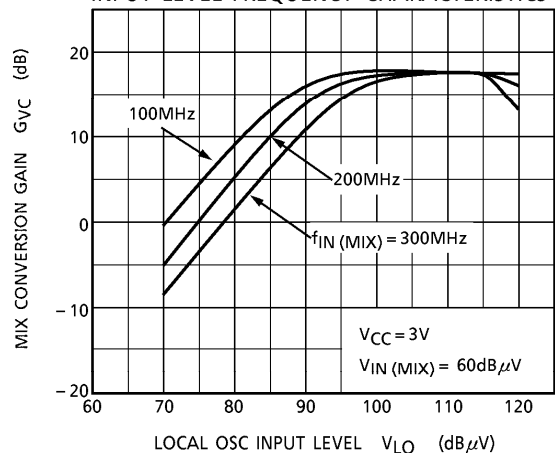
When  $V_{CC} = 3\text{V}$ , battery save switch on  $V_{CC}$  side, SW1 on SG3 side  
([A] side only when  $G_{VC}$  tested)



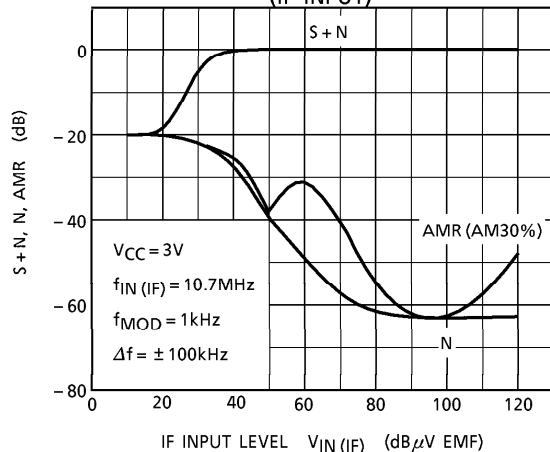
MIX CONVERSION GAIN –  
LOCAL OSC INPUT LEVEL



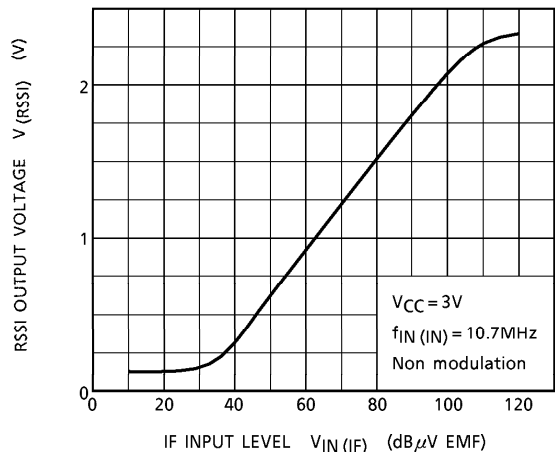
MIX CONVERSION GAIN – LOCAL OSC  
INPUT LEVEL FREQUENCY CHARACTERISTICS



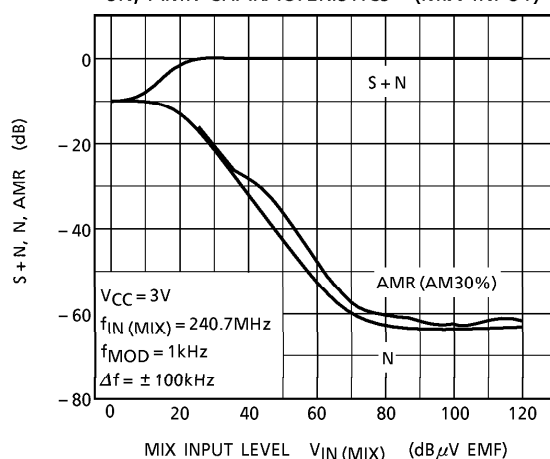
SN, AMR CHARACTERISTICS  
(IF INPUT)



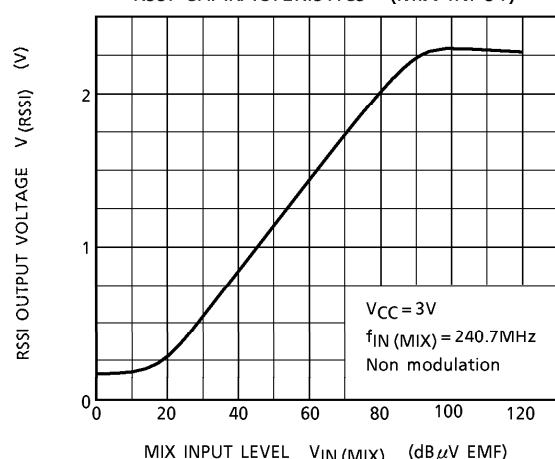
RSSI CHARACTERISTICS (IF INPUT)



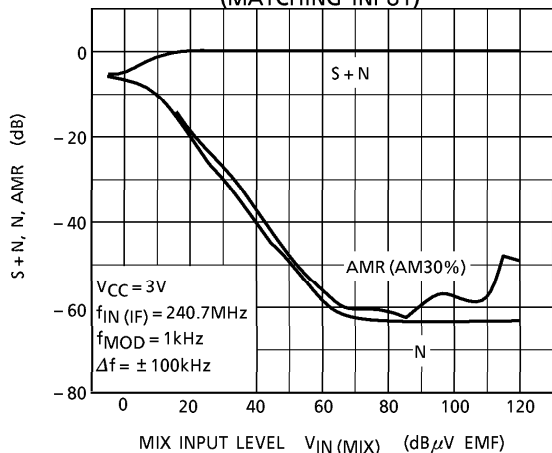
SN, AMR CHARACTERISTICS (MIX INPUT)



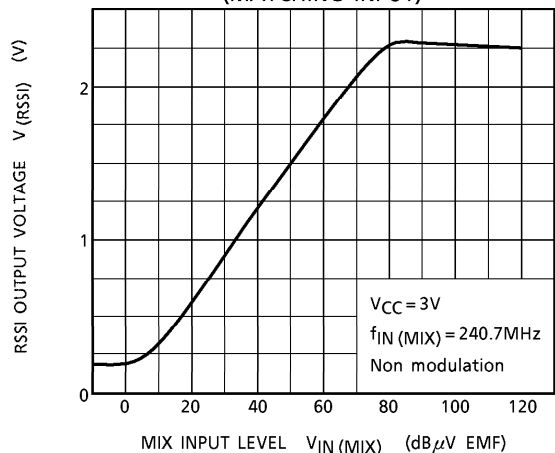
RSSI CHARACTERISTICS (MIX INPUT)



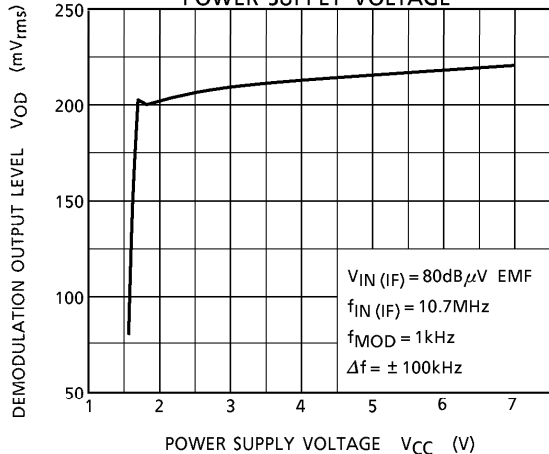
SN, AMR CHARACTERISTICS  
(MATCHING INPUT)



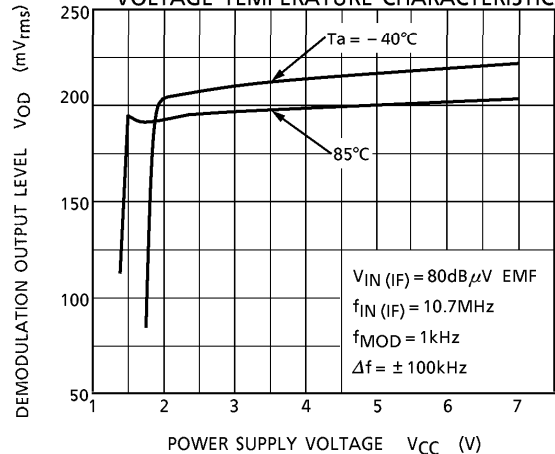
RSSI CHARACTERISTICS  
(MATCHING INPUT)



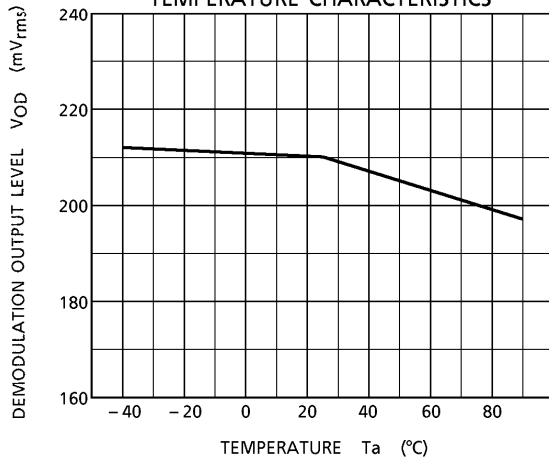
DEMODULATION OUTPUT LEVEL –  
POWER SUPPLY VOLTAGE



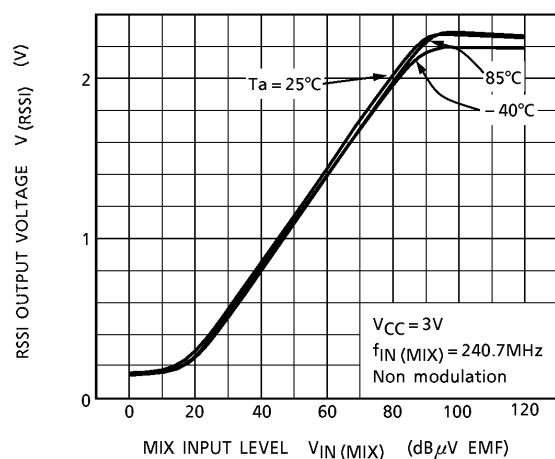
DEMODULATION OUTPUT LEVEL – POWER SUPPLY  
VOLTAGE TEMPERATURE CHARACTERISTICS

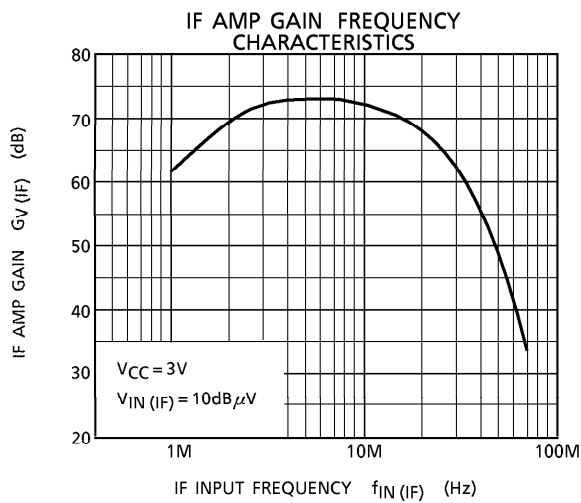


DEMODULATION OUTPUT LEVEL  
TEMPERATURE CHARACTERISTICS

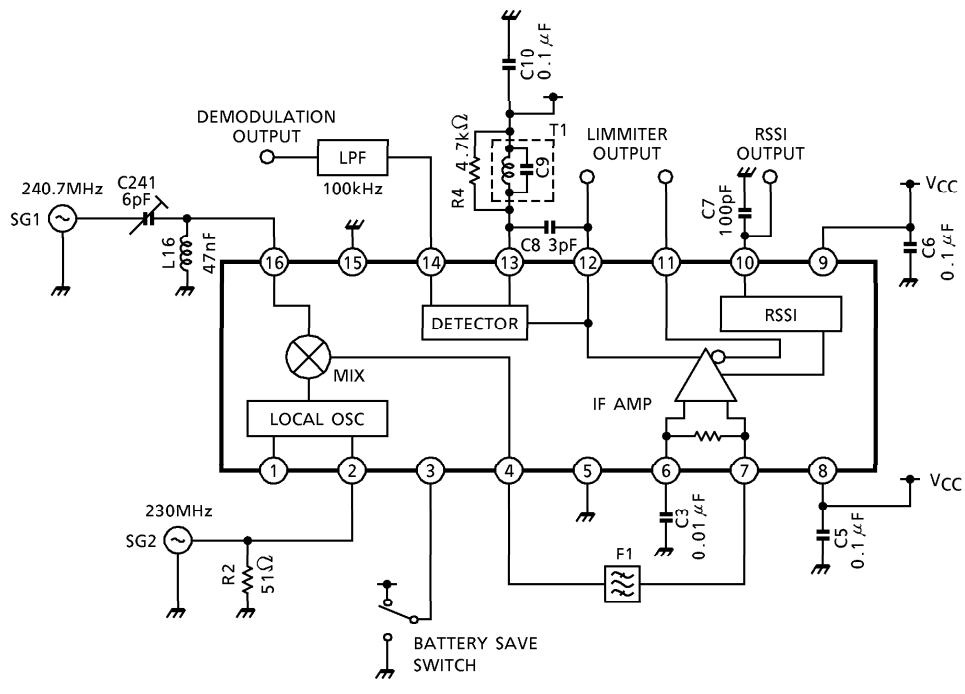


RSSI TEMPERATURE CHARACTERISTICS





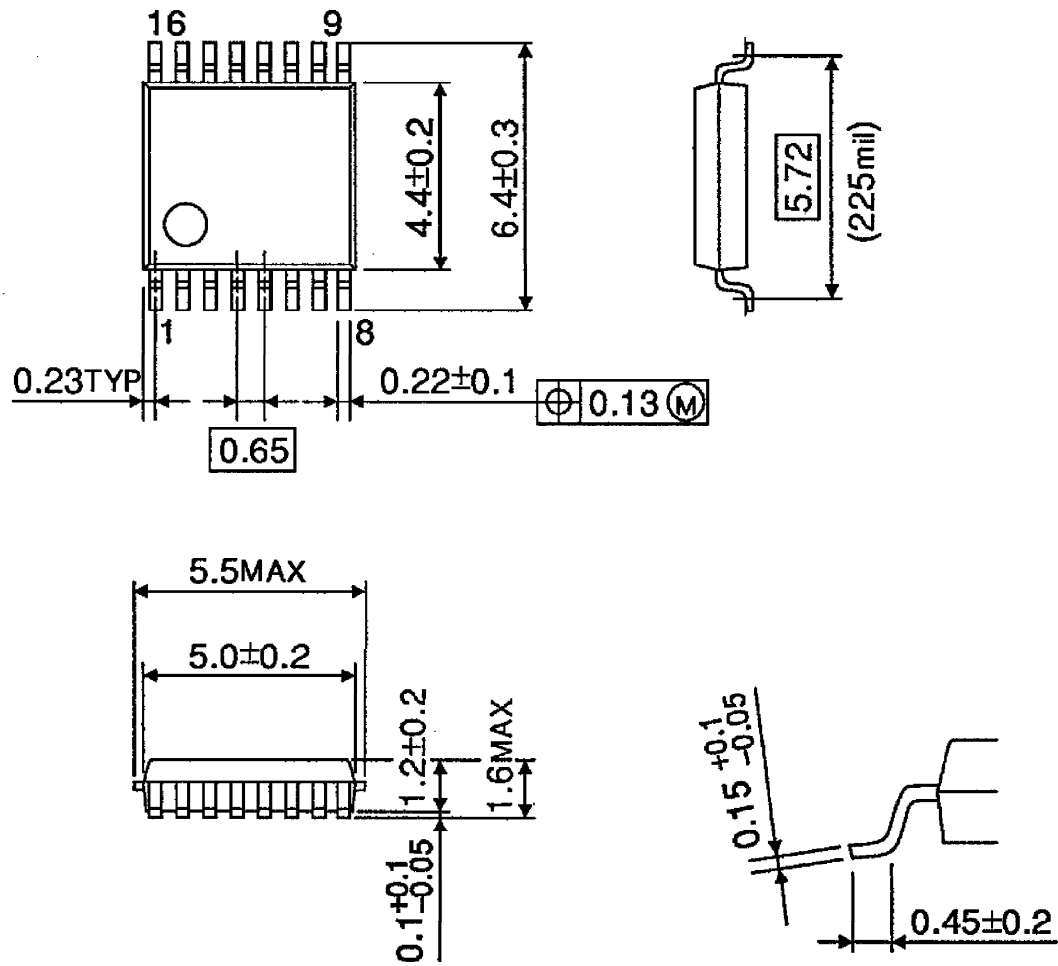
## APPLICATION CIRCUIT



- T1 : 4162-JPS-024  
(SUMIDA ELECTRIC CO., LTD.)
- F1 : CFEC10.7MK1  
(MURATA MFG. CO., LTD.)

PACKAGE DIMENSIONS  
SSOP16-P-225-0.65B

Unit : mm



Weight : 0.09g (Typ.)

About solderability, following conditions were confirmed

- Solderability
- (1) Use of Sn-63Pb solder bath
  - Solder bath temperature = 230
  - Dipping time = 5seconds
  - The number of times = once
  - Use of R-type flux
- (2) Use of Sn- 3.0Ag-0.5Cu solder bath
  - Solder bath temperature = 245
  - Dipping time = 5seconds
  - The number of times = once
  - Use of R-type flux

## RESTRICTIONS ON PRODUCT USE

000707EBA

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